# Abstracts

## Distributed GaAs FET Circuit Model for Broadband and Millimeter Wave Applications

*R. LaRue, C. Yuen and G. Zdasiuk. "Distributed GaAs FET Circuit Model for Broadband and Millimeter Wave Applications." 1984 MTT-S International Microwave Symposium Digest 84.1 (1984 [MWSYM]): 164-166.*

In this distributed. paper, the Z-parameters of a fully equivalent circuit MESFET model are presented as simple, closed-form expressions. The benefit of this new model is to extend the frequency range of accurate, predicted device performance beyond that of a simple lumped element model . Comparison with the simpler circuit model shows differences at frequencies beyond 18 GHz for a 285-micron x 0.5-micron GaAs MESFET.

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